

Schottky Barrier Diodes

MA3XD14E

■ Features

- Mini type 3-pin package
- Low forward rise voltage V_F ($V_F < 0.4$ V)
- Cathode common type

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	20	V
Repetitive peak reverse-voltage	I_{RRM}	20	V
Non-repetitive peak forward-surge-current (Note 2)	I_{FSM}	1	A
Forward current (DC)	Single	100	mA
	Double (Note 1)	70	
Peak forward current	Single	300	mA
	Double (Note 1)	200	
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to+ 150	$^\circ\text{C}$

Note

1 : The value for operating one chip

2 : The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 10$ V			20	μA
Forward voltage (DC)	V_F	$I_F = 5$ mA			0.27	V
		$I_F = 100$ mA			0.40	V
Terminal capacitance	C_t	$V_R = 0$ V, $f = 1$ MHz		25		pF
Reverse recovery time*	t_{rr}	$I_F = I_R = 100$ mA, $I_{rr} = 10$ mA, $R_L = 100 \Omega$		3.0		ns

Note

1. This product is sensitive to electric shock (static electricity, etc.).Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment.

2. Rated input/output frequency: 400 MHz

3. * : t_{rr} measuring circuit

■ Marking

Marking	M5H
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